

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISOM8110DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8110DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8110
ISOM8111DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8111DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8111
ISOM8112DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8112DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8112
ISOM8113DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8113DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8113
ISOM8115DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISOM8115DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8115DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8115DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8115DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8115DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8115DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8115
ISOM8116DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8116DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8116
ISOM8117DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8117DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8117
ISOM8118DFGR	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFGR.A	Active	Production	SOIC (DFG) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFHR	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFHR.A	Active	Production	SOIC (DFH) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFSR	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFSR.A	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118
ISOM8118DFSR.B	Active	Production	SOIC (DFS) 4	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	8118

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) RoHS values: Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF ISOM8110, ISOM8111, ISOM8112, ISOM8113, ISOM8115, ISOM8116, ISOM8117, ISOM8118 :

- Automotive : [ISOM8110-Q1](#), [ISOM8111-Q1](#), [ISOM8112-Q1](#), [ISOM8113-Q1](#), [ISOM8115-Q1](#), [ISOM8116-Q1](#), [ISOM8117-Q1](#), [ISOM8118-Q1](#)
- Enhanced Product : [ISOM8110-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications